



IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for manufacturing a semiconductor device equipped with a capacitor in which a dielectric film is used, wherein a conductive complex oxide having an exposed top surface is used as a mask material when the dielectric film is subjected to reactive ion etching, and the mask material, which is in direct contact with the dielectric film, is used as an upper electrode of the capacitor after the reactive ion etching is performed.

Claim 2 (Original): The method according to claim 1, wherein the complex oxide contains  $\text{SrRuO}_3$  as a main component.

Claim 3 (Previously Presented): The method according to claim 1, wherein the complex oxide is a conductive oxide.

Claim 4 (Cancelled).

Claim 5 (Original): The method according to claim 1, wherein the dielectric film contains PZT as a main component.

Claim 6 (Previously Presented): The method according to claim 1, wherein Pt, Ir, Ru,  $\text{IrO}_2$ ,  $\text{RuO}_2$ , or a laminated structure or a mixture of them is used as a material of a lower electrode of the capacitor.

Claim 7 (Withdrawn): A semiconductor device equipped with a capacitor in which a dielectric film is used, wherein a mask material used in etching the dielectric film is prepared as an electrode of the capacitor.

Claim 8 (Withdrawn): The semiconductor device according to claim 7, wherein the dielectric film is a ferroelectric film.

Claim 9 (Withdrawn): The device according to claim 8, wherein the ferroelectric film is PZT.

Claim 10 (Withdrawn): The device according to claim 7, wherein Pt, Ir, Ru, IrO<sub>2</sub>, RuO<sub>2</sub>, or a laminated structure or a mixture of them is used as a material of the electrode of the capacitor.